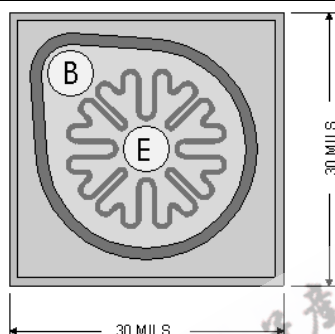


**Chip Type 2C3501**  
**Geometry 5620**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N3498, 2N3499, 2N3500,**  
**2N3501**



[Request Quotation](#)

Chip type **2C3501** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:** Designed for switching and amplifier applications.

**Part Numbers:**

[2N3498](#), [2N3498L](#), [2N3499](#), [2N3499L](#), [2N3500](#),  
[2N3500L](#), [2N3501](#), [2N3501L](#)

**Features:**

### Mechanical Specifications

Metallization	Top	Al - 22.5 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	5.0 mils diameter
	Base	5.0 mils diameter
Die Thickness	8 mils nominal	
Chip Area	30 mils x 30 mils	
Top Surface	Silox Passivated	

### Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10.0 \text{ mA}$ , $I_B = 0$	150	---	V dc
$BV_{CBO}$	$I_C = 10 \mu\text{A}$ , $I_E = 0$	150	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}$ , $I_C = 0$	6.0	---	V dc
$I_{CBO}$	$V_{CB} = 75 \text{ Vc}$ , $I_E = 0$	---	50	nA
$h_{FE}$	$I_C = 150 \text{ mA dc}$ , $V_{CE} = 10.0 \text{ V}$	100	300	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*